CSD19538Q2 100V N 沟道 NexFET™ 功率 MOSFET

1 特性

- 超低 Q_g 和 Q_{gd}
- 低热阻
- 雪崩额定值
- 无铅
- 符合 RoHS 标准
- 无卤素
- 小外形尺寸无引线 (SON) 2mm x 2mm 塑料封装

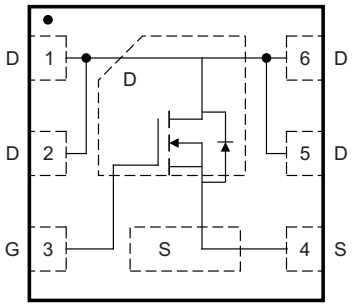
2 应用

- 以太网供电 (PoE)
- 电源设备 (PSE)
- 电机控制

3 说明

这款 100V、49mΩ、采用 2mm × 2mm SON 封装的 NexFET™功率 MOSFET 被设计成在功率转换应用中大大降低 损耗。

顶视图



P0108-01

产品概要

T_A=25°C		典型值		单位
V_{DS}	漏源电压	100		V
Q_g	栅极电荷总量 (10V)	4.3		nC
Q_{gd}	栅极电荷（栅极到漏极）	0.8		nC
$R_{DS(on)}$	漏源导通电阻	V_{GS} = 6V	58	mΩ
		V_{GS} = 10V	49	
$V_{GS(th)}$	阈值电压	3.2		V

器件信息(1)

器件	数量	包装介质	封装	运输
CSD19538Q2	3000	7 英寸卷带	SON 2.00mm x 2.00mm 塑料封装	卷带封装
CSD19538Q2T	250			

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

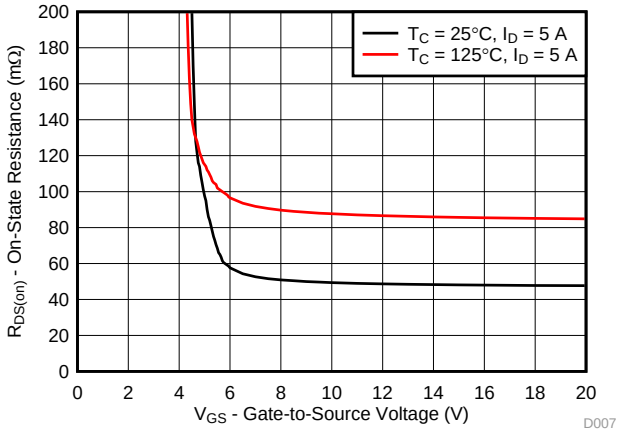
绝对最大额定值

T_A = 25°C		值	单位
V_{DS}	漏源电压	100	V
V_{GS}	栅源电压	±20	V
I_D	持续漏极电流（受封装限制）	14.4	A
	持续漏极电流（受芯片限制），T_C = 25°C 时测得	13.1	
	持续漏极电流(1)	4.6	
I_{DM}	脉冲漏极电流(2)	34.4	A
P_D	功率耗散(1)	2.5	W
	功率耗散，T_C = 25°C	20.2	
T_J, T_{stg}	工作结温，储存温度	-55 至 150	°C
E_{AS}	雪崩能量，单脉冲 I_D = 12.6A，L = 0.1mH，R_G = 25Ω	8	mJ

(1) $R_{\theta JA}$ = 50°C/W，这是在一块厚度为 0.06 英寸环氧树脂 (FR4) 印刷电路板 (PCB) 上的 1 英寸^2，2 盎司铜焊盘上测得的典型值。

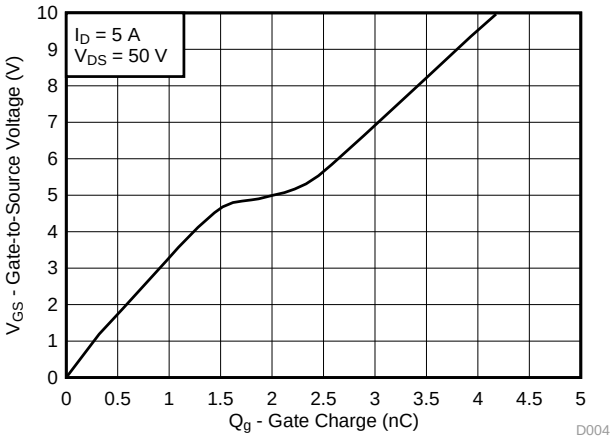
(2) 最大 $R_{\theta JC}$ = 6.2°C/W，脉冲持续时间 ≤ 100µs，占空比 ≤ 1%。

$R_{DS(on)}$ 与 V_{GS} 对比



中的测试电压 V_{DS} 从 100V 更改为 50V

栅极电荷



目录

4 修订历史记录

Changes from Original (July 2016) to Revision A **Page**

- 已更改 将栅极电荷曲线 ... 2
- Changed test voltage V_{DS} from 100 V : to 50 V in Figure 4 ... 5

5 Specifications

5.1 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

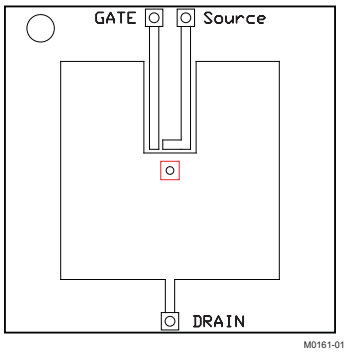
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0 V, I_D = 250 μA	100			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0 V, V_{DS} = 80 V			1	μA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.8	3.2	3.8	V
$R_{DS(on)}$	Drain-to-source on resistance	V_{GS} = 6 V, I_D = 5 A		58	72	mΩ
		V_{GS} = 10 V, I_D = 5 A		49	59	
g_{fs}	Transconductance	V_{DS} = 10 V, I_D = 5 A		19		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DS} = 50 V, f = 1 MHz		349	454	pF
C_{oss}	Output capacitance			69	90	pF
C_{rss}	Reverse transfer capacitance			12.6	16.4	pF
R_G	Series gate resistance			4.6	9.2	Ω
Q_g	Gate charge total (10 V)	V_{DS} = 50 V, I_D = 5 A		4.3	5.6	nC
Q_{gd}	Gate charge gate-to-drain			0.8		nC
Q_{gs}	Gate charge gate-to-source			1.6		nC
$Q_{g(th)}$	Gate charge at V_{th}			1.0		nC
Q_{oss}	Output charge	V_{DS} = 50 V, V_{GS} = 0 V		12.3		nC
$t_{d(on)}$	Turnon delay time	V_{DS} = 50 V, V_{GS} = 10 V, I_{DS} = 5 A, R_G = 0 Ω		5		ns
t_r	Rise time			3		ns
$t_{d(off)}$	Turnoff delay time			7		ns
t_f	Fall time			2		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_{SD} = 5 A, V_{GS} = 0 V		0.85	1.0	V
Q_{rr}	Reverse recovery charge	V_{DS}= 50 V, I_F = 5 A, di/dt = 300 A/μs		94		nC
t_{rr}	Reverse recovery time			32		ns

5.2 Thermal Information

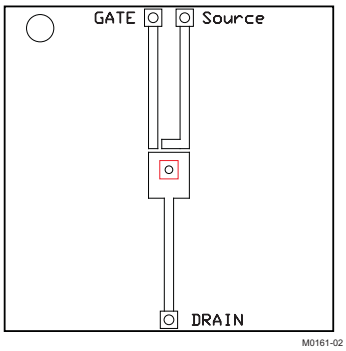
T_A = 25°C (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance(1)			6.2	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance(1)(2)			65	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu pad on a 1.5-in × 1.5-in (3.81-cm × 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA}$ = 65°C/W when mounted on 1 in^2 (6.45 cm^2) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA}$ = 250°C/W when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

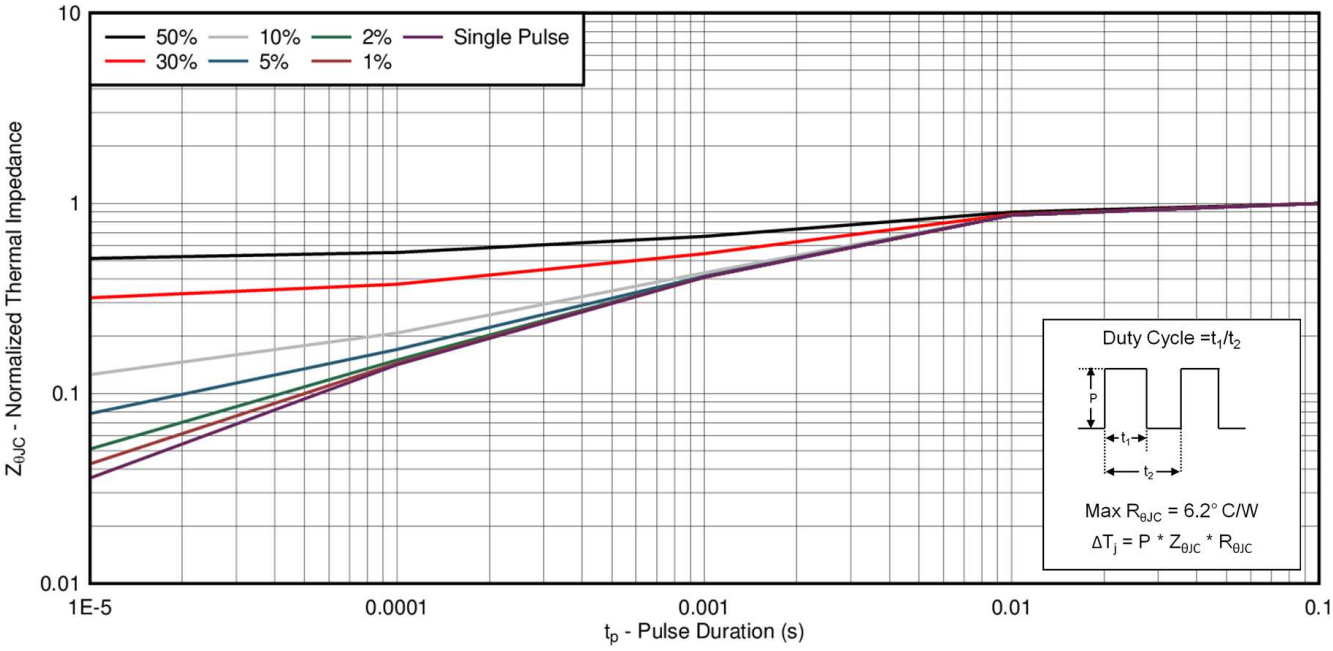


Figure 1. Transient Thermal Impedance

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

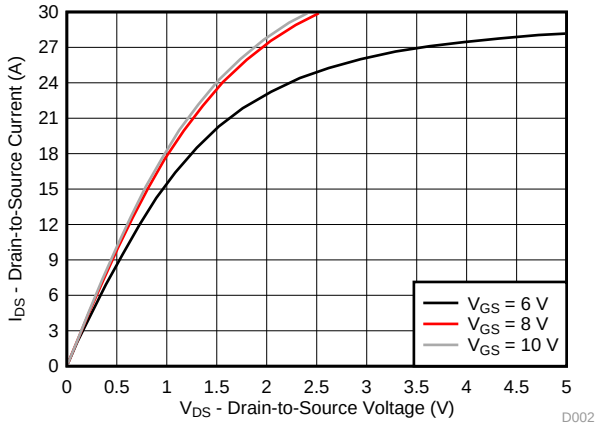


Figure 2. Saturation Characteristics

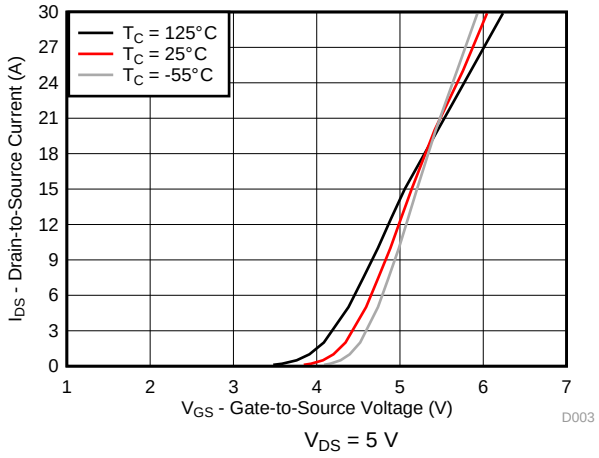


Figure 3. Transfer Characteristics

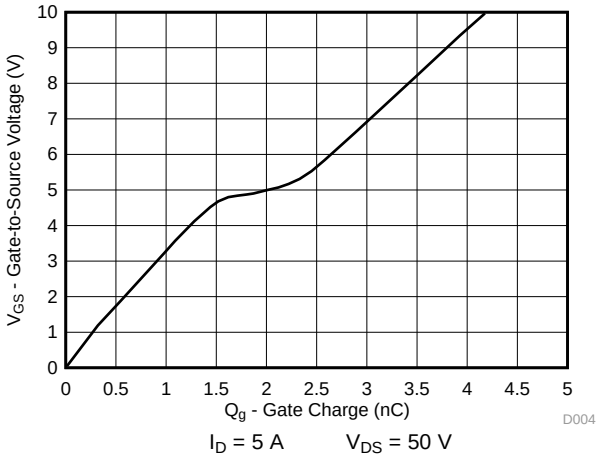


Figure 4. Gate Charge

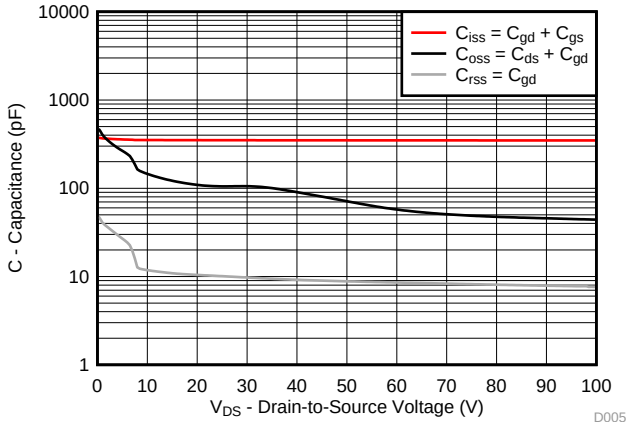


Figure 5. Capacitance

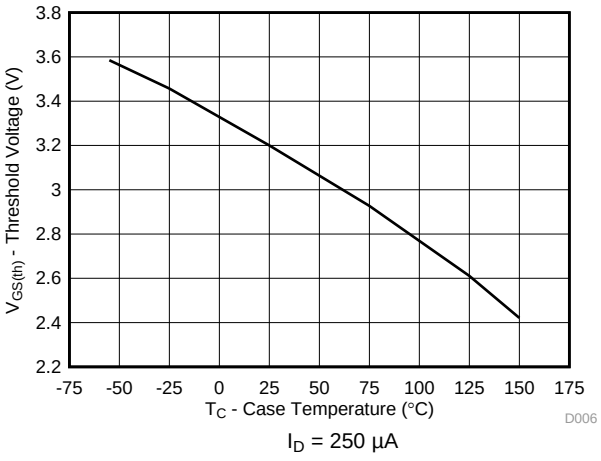


Figure 6. Threshold Voltage vs Temperature

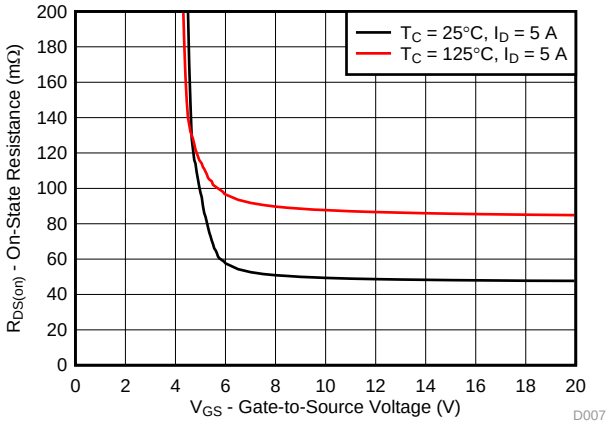


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

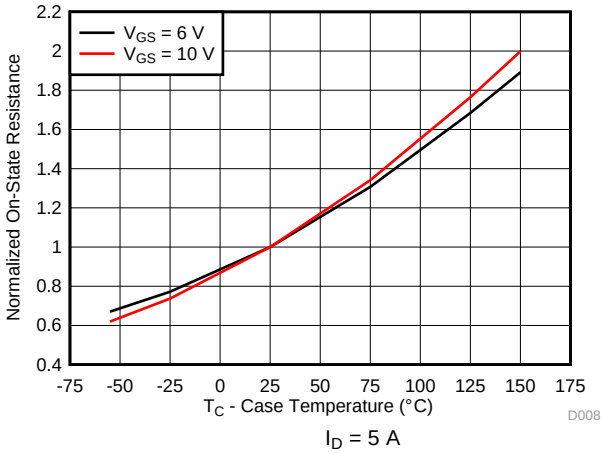


Figure 8. Normalized On-State Resistance vs Temperature

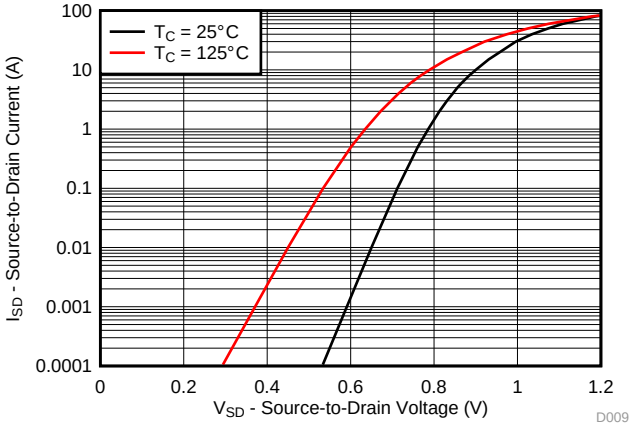


Figure 9. Typical Diode Forward Voltage

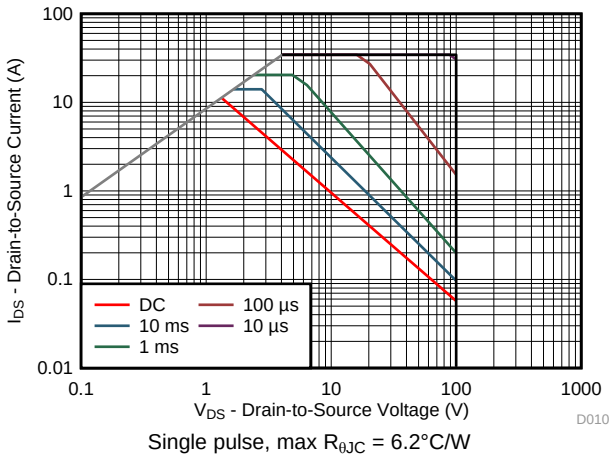


Figure 10. Maximum Safe Operating Area

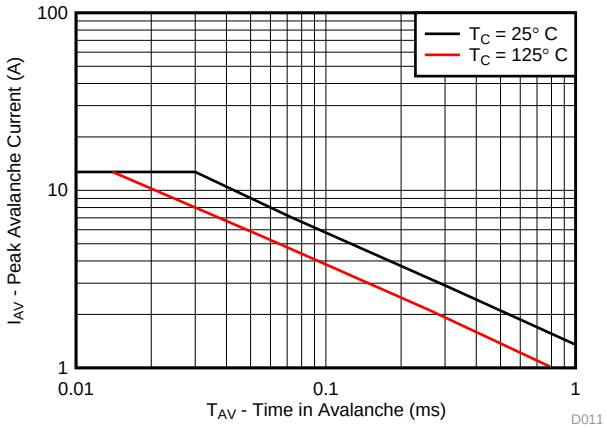


Figure 11. Single Pulse Unclamped Inductive Switching

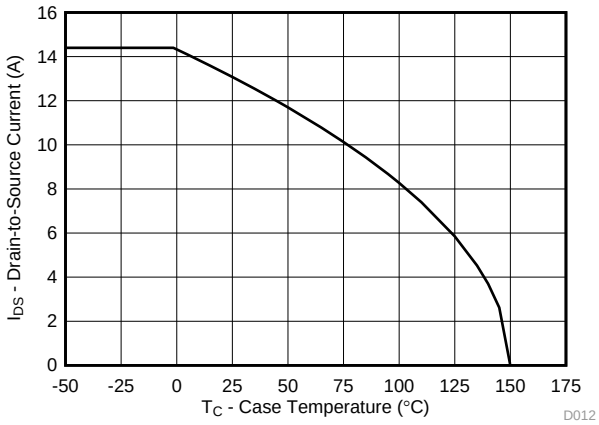


Figure 12. Maximum Drain Current vs Temperature

6 器件和文档支持

6.1 接收文档更新通知

如需接收文档更新通知，请访问 www.ti.com.cn 网站上的器件产品文件夹。点击右上角的*提醒我* (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

6.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 商标

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.4 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

6.5 Glossary

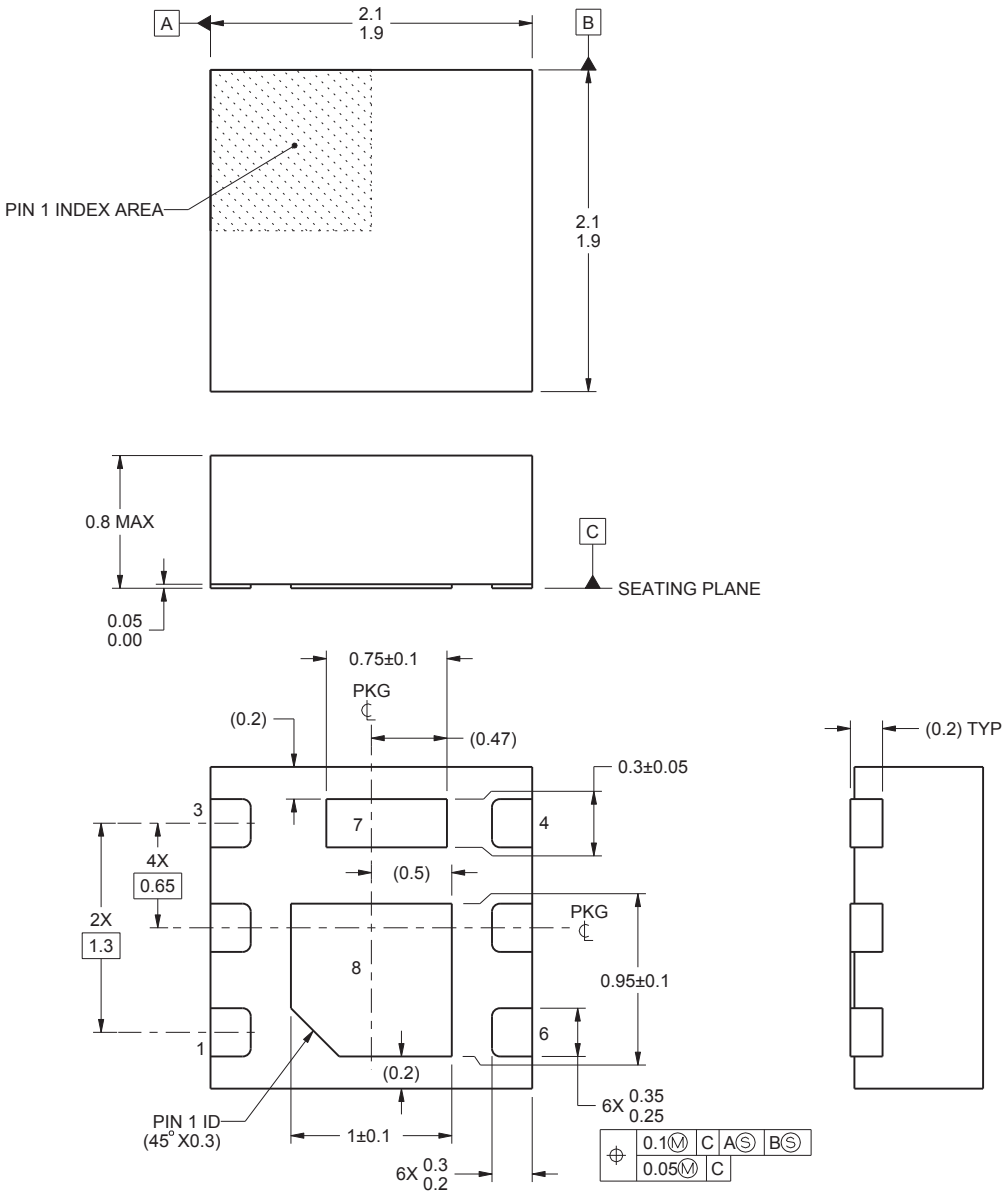
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。要获得这份数据表的浏览器版本，请查阅左侧的导航栏。

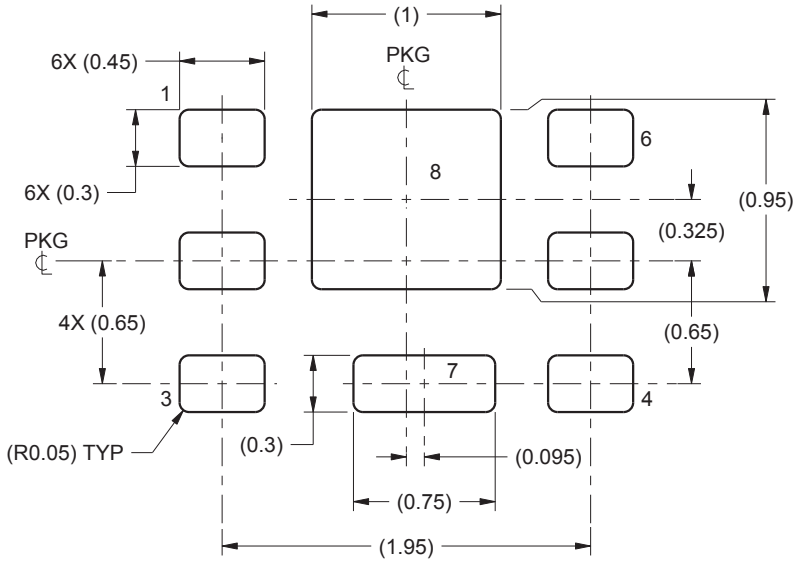
7.1 Q2 封装尺寸

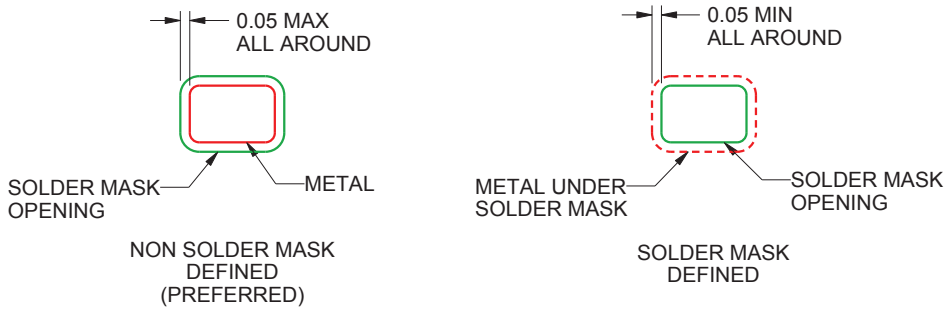


1. 所有线性尺寸的单位均为毫米。括号中的任何尺寸仅供参考。尺寸和容限值遵循 ASME Y14.5M。
2. 本图纸如有变更，恕不通知。
3. 封装散热盘必须在印刷电路板上焊接，包装散热和机械性能。

Q2 封装尺寸 (接下页)

7.1.1 建议 PCB 布局

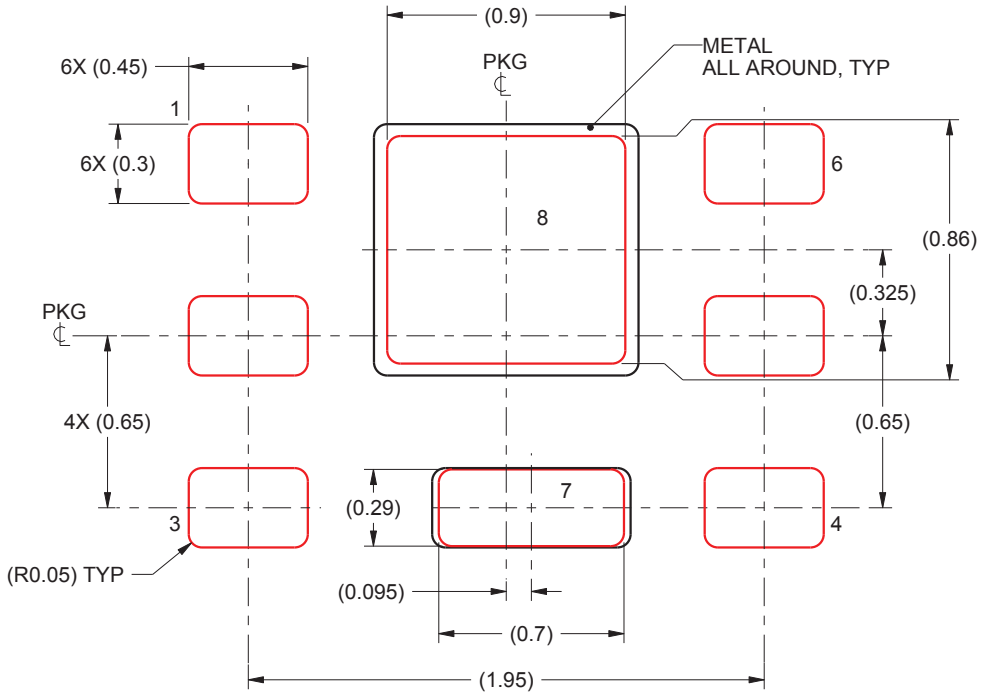




1. 有关针对 PCB 设计的建议电路布局布线，请参见*《通过 PCB 布局布线技巧来减少振铃》*（文献编号：SLPA005）。
2. 此封装设计用于焊接到电路板的散热焊盘上。更多信息，请参见*《QFN/SON PCB 连接》*（文献编号：SLUA271）。

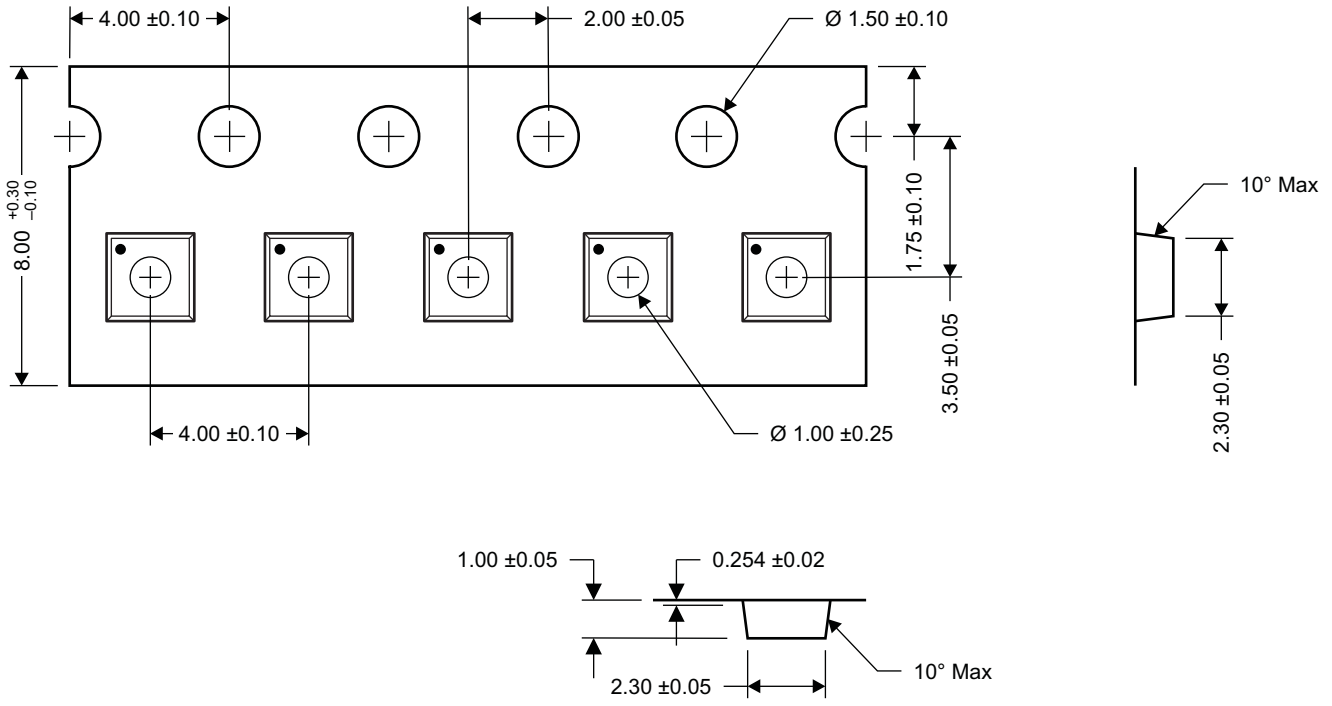
Q2 封装尺寸 (接下页)

7.1.2 推荐的模版布局



1. 所有线性尺寸的单位均为毫米。
2. 具有漏斗形壁和圆角的激光切割窗孔将提供更佳的焊锡膏脱离。IPC-7525 可能提供其他替代性设计建议。

7.2 Q2 卷带信息



Notes: 1. 测自链齿孔中心线到孔眼中心线。
2. 10 个链齿孔的累积容差为 ±0.2。
3. 提供了其他材料。
4. 卷带的 SR 典型值最大为 10^9 OHM/SQ。
5. 所有尺寸单位均为 mm，除非另有说明。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD19538Q2	ACTIVE	WSON	DQK	6	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 150	1958	Samples
CSD19538Q2R	ACTIVE	WSON	DQK	6	10000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958	Samples
CSD19538Q2T	ACTIVE	WSON	DQK	6	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 150	1958	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

GENERIC PACKAGE VIEW

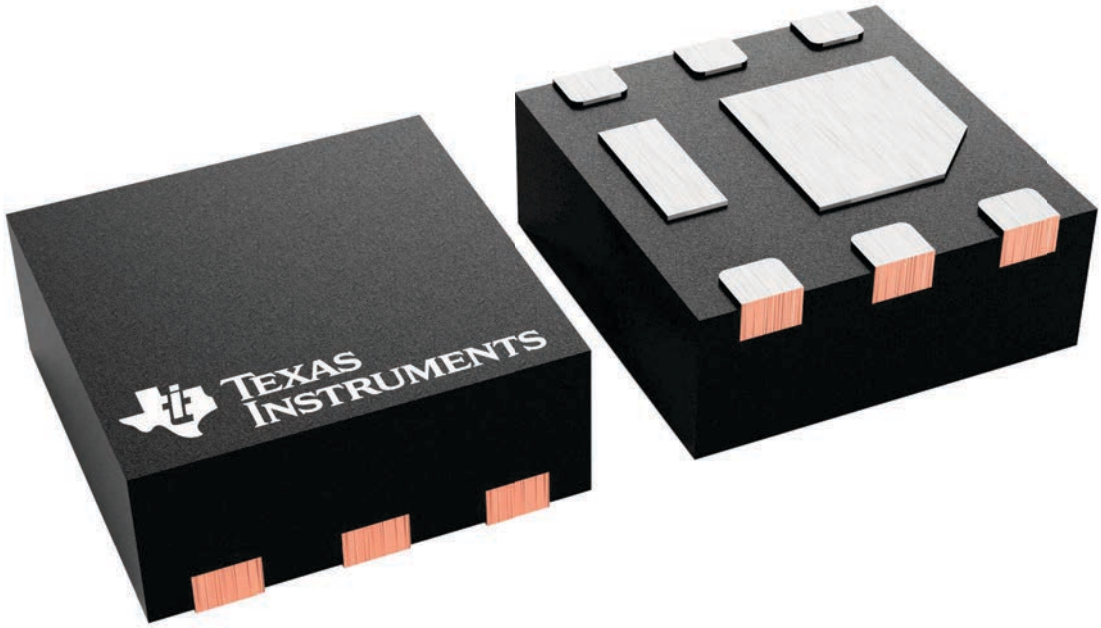
DQK 6

WSON - 0.8 mm max height

2 x 2, 0.65 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



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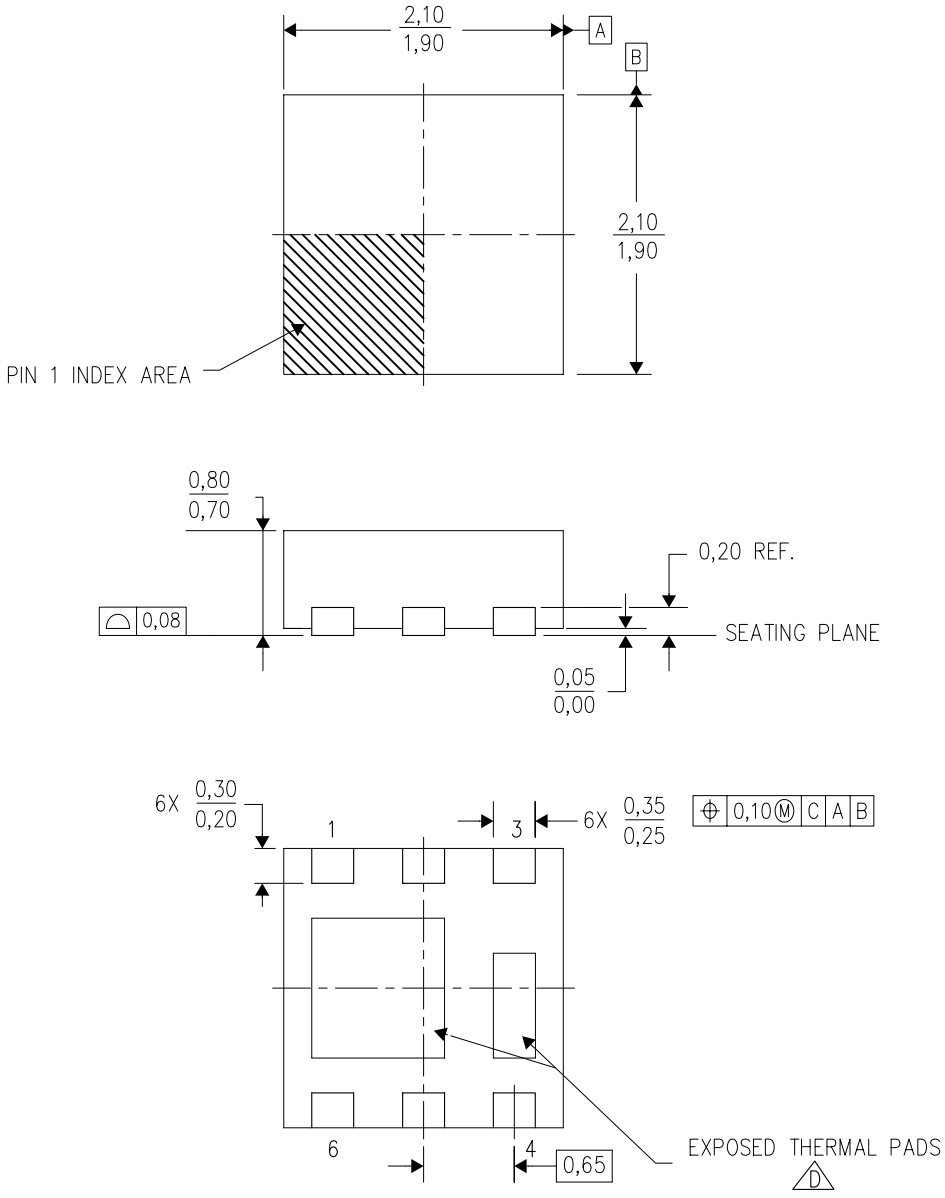
DQK (S–PWSON–N6) PLASTIC SMALL OUTLINE NO–LEAD



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NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Small Outline No–Lead (SON) package configuration.
D. The package thermal pads must be soldered to the board for thermal and mechanical performance.

THERMAL PAD MECHANICAL DATA

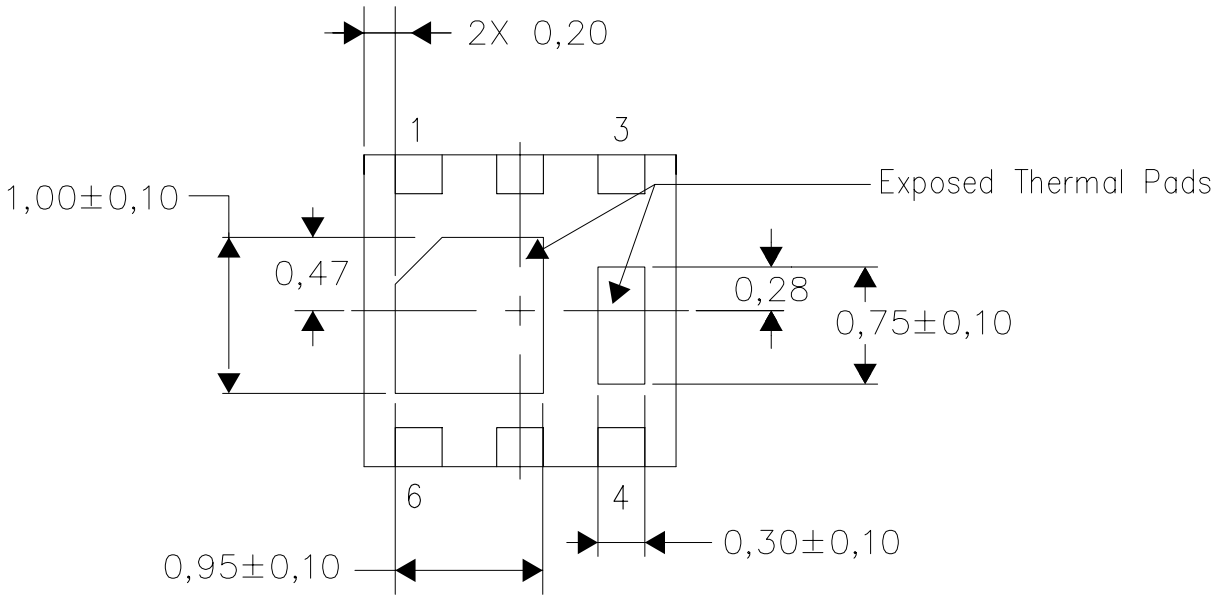
DQK (S–PWSON–N6)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No–Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

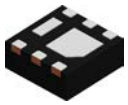


Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

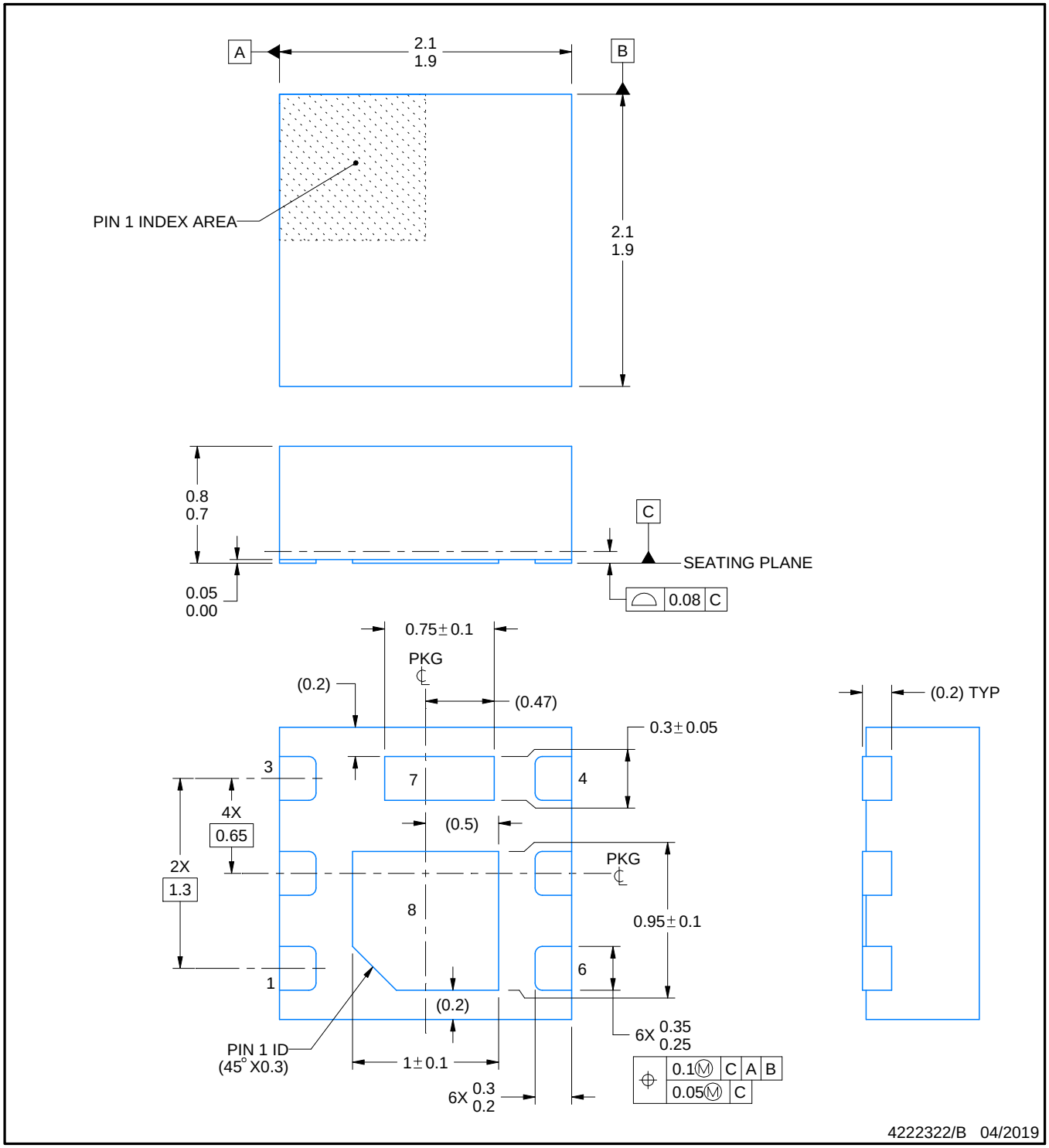
DQK0006C



PACKAGE OUTLINE

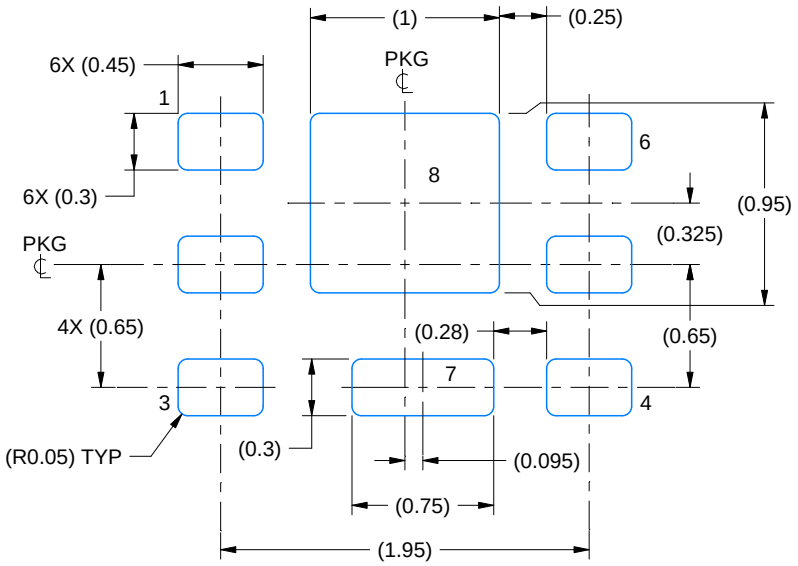
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

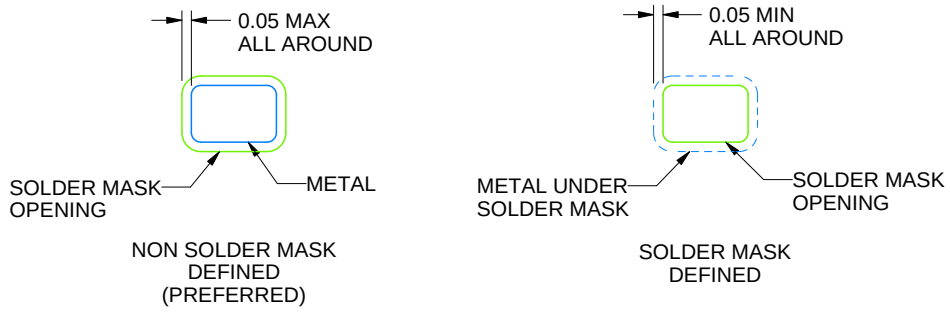


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pads must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:25X



SOLDER MASK DETAILS

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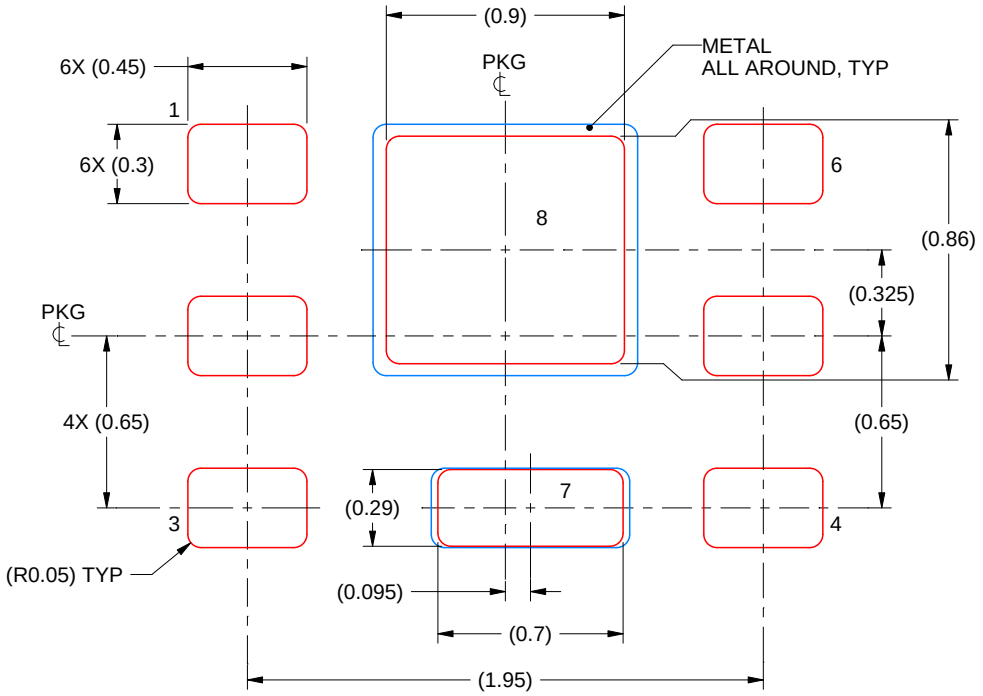
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA
PAD 7: 90%, PAD 8: 81%
SCALE:35X

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NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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